

Product Overview

NGTB40N65IHR: IGBT, Monolithic with Reverse Conducting Diode, 650 V, 40 A

For complete documentation, see the data sheet.

This Insulated Gate Bipolar Transistor (IGBT) features robust and cost effective Field Stop (FS2) trench construction with a monolithic RC Diode. It provides a cost effective Solution for applications where diode losses are minimal. The IGBT is optimized for low conduction losses (low V_{CEsat}) and is well suited for resonant or soft switching applications.

Features

- Extremely Efficient Trench with Fieldstop Technology
- Low Conduction Loss Design for Soft Switching Application
- Reduced Power Dissipation in Induction Heating
- Reliable and Cost Effective Single Die Solution
- This is a Pb-Free Device

Applications

- Inductive Heating
- Air Conditioning PFC
- Welding

End Products

- Industrial

For more information please contact your local sales support at www.onsemi.com.

Created on: 2/22/2019